

## ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting device comprises:  
a substrate; an n-type layer provided on the substrate  
5 and made of a nitride semiconductor material; a multiple  
quantum well structure active layer including a plurality  
of well layers each made of  $\text{In}_x\text{Ga}_{(1-x-y)}\text{Al}_y\text{N}$  ( $0 \leq x$ ,  $0 \leq y$ ,  $x+y < 1$ )  
and a plurality of barrier layers each made of  $\text{In}_s\text{Ga}_{(1-s-t)}\text{Al}_t\text{N}$  ( $0 \leq s$ ,  $0 \leq t$ ,  $s+t < 1$ ), the multiple quantum well  
10 structure active layer being provided on the n-type layer;  
and a p-type layer provided on the multiple quantum well  
structure active layer and made of a nitride semiconductor  
material. The p-type layer contains hydrogen, and the  
hydrogen concentration of the p-type layer is greater than  
15 or equal to about  $1 \times 10^{16}$  atoms/cm<sup>3</sup> and less than or equal  
to about  $1 \times 10^{19}$  atoms/cm<sup>3</sup>.

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